

→ FEATURED PRODUCT

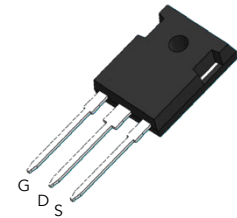
Good-Ark Semiconductor GSFA20106

200V, 106A, 9.4mΩ N-Channel MOSFET with Ultra-low $R_{DS(ON)}$ and Qgd in TO-247 Package

Good-Ark Semiconductor introduces GSFA20106, a 200V,106A, 9.4mΩ, N-Channel MOSFET with ultra-low $R_{DS(ON)}$ and Qgd ideal for uni-directional high frequency switching applications. The GSFA20106 utilizes the latest deep trench technologies and advance process techniques to achieve excellent $R_{DS(ON)}$, lower gate charge, and a high repetitive avalanche rating. Packaged in the TO-247 package, this device is suitable for DC-DC converters, BMS, Micro-inverters, on board power for servers, motor control and high-power density point of load.

BENEFITS

- Low gate-charge
- Best-in-class on-resistance (9.4mΩ Typ.)
- High power density and efficiency
- Low switching and drive losses
- Low reverse recovery charge



TO-247 Package

BENEFITS

- Reduces overshoot
- Reduces the number of MOSFETs in parallel
- Increases system reliability while achieving cost-saving
- Energy efficient

APPLICATIONS

- DC-DC conversion
- BMS and Servers
- Power tools and Class-D audios
- Motor controls

Free samples available for immediate testing.
 Contact us at: (+1) 631-319-1858 or
inquiry@goodarksemi.com

KEYSPECIFICATIONS

Part Number	I_D	V_{DS}	V_{GS}	$V_{GS} (mV)$ @ $V_{DS}=V_{GS}$, $I_D=250\mu A$		$R_{DS(ON)}$ @ $I_D=88A$ $V_{GS}=10V$		Q_{GD} @ $V_{DD}=100V$, $I_D=44A$ $V_{GS}=10V$	Q_G @ $V_{DD}=100V$, $I_D=44A$ $V_{GS}=10V$	C_{iss}	T_J, T_{STG}
	Max (A)	Max (V)	Max (V)	Min (V)	Max (V)	Typ. (mΩ)	Max (mΩ)	Typ. (nC)	Typ. (nC)	(pF)	(°C)
GSFA20106	106	200	±20	2.0	4.0	9.4	10.7	7.9	64	4720	-55 to +150

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